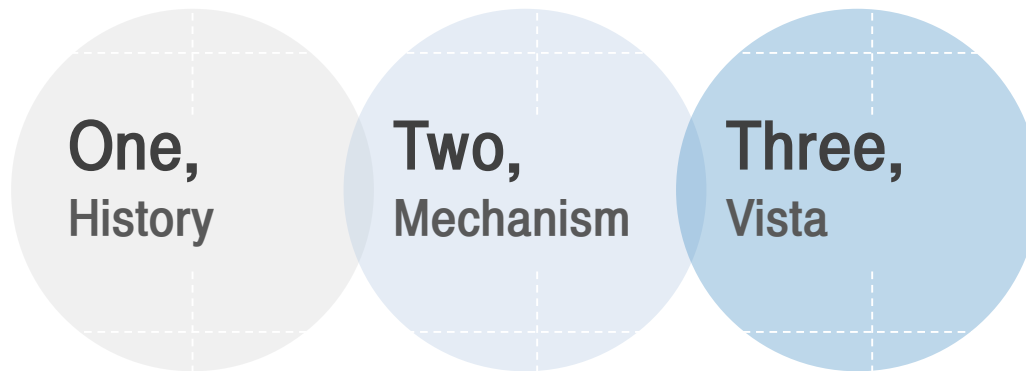


Advanced Magnetic Materials

'Spin Seebeck Effect'

2015311476 Lee Hwijong

--- Index



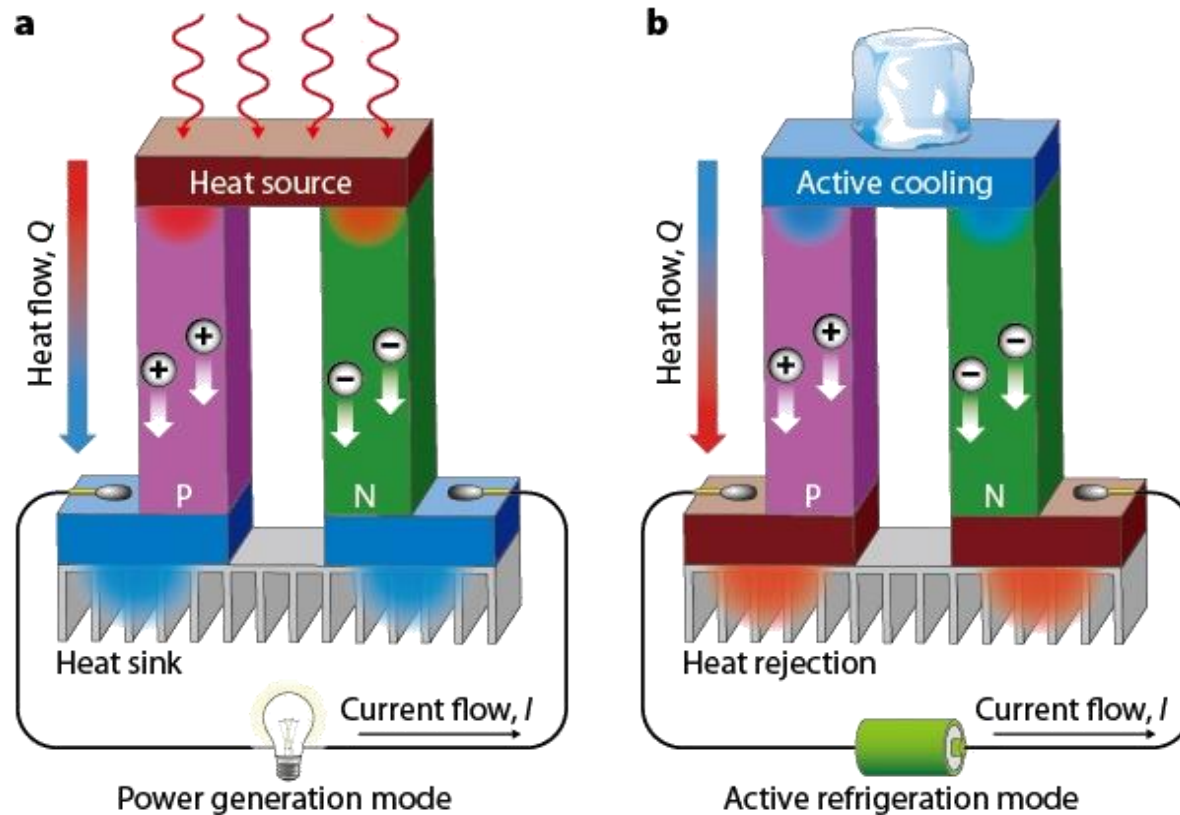
1

History

Thermoelectric Effect, and Spin Seebeck Effect(SSE)

Thermoelectric Effect

[Temperature gradient to electric voltage and vice versa]

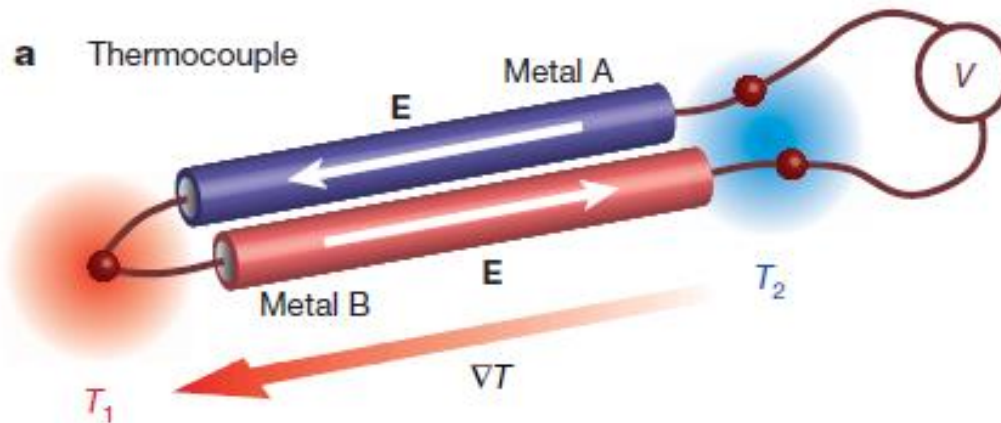


Seebeck effect (1821)

Peltier effect (1843)

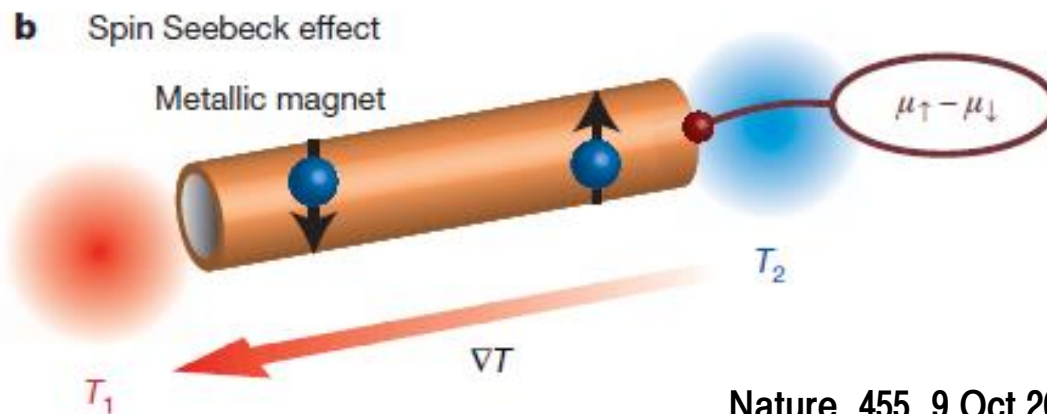
Spin Seebeck Effect (SSE)

[Temperature gradient to spin voltage]



Different S between A and B

→ Voltage(V) $\propto \Delta T$



Different S between \uparrow and \downarrow

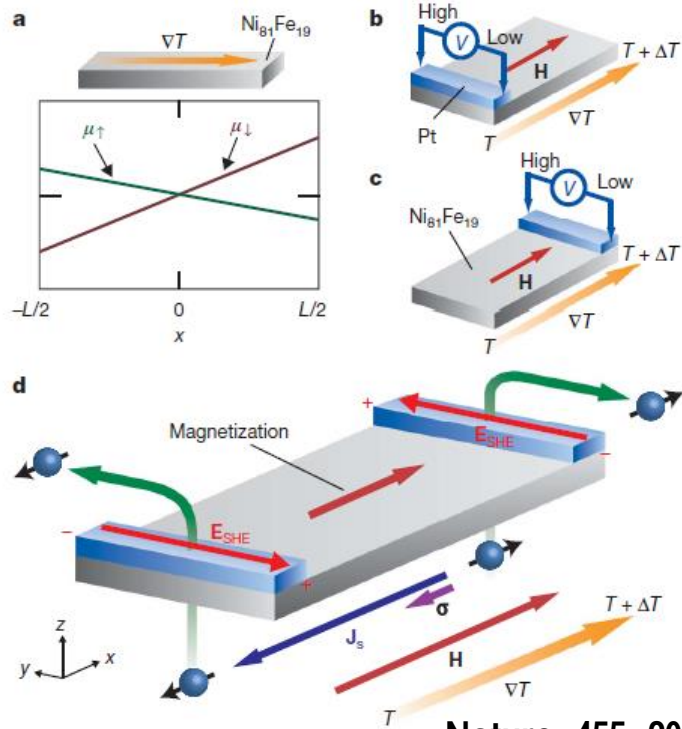
→ Spin Voltage $\propto \Delta T$

= Spin current potential

= $\mu_{\uparrow} - \mu_{\downarrow}$

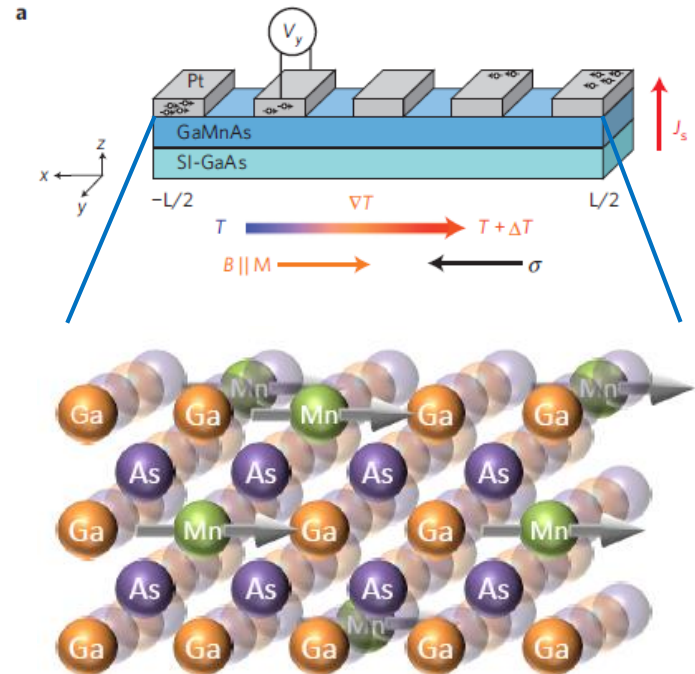
Spin Seebeck Effect (SSE)

Metallic Magnet (2008)



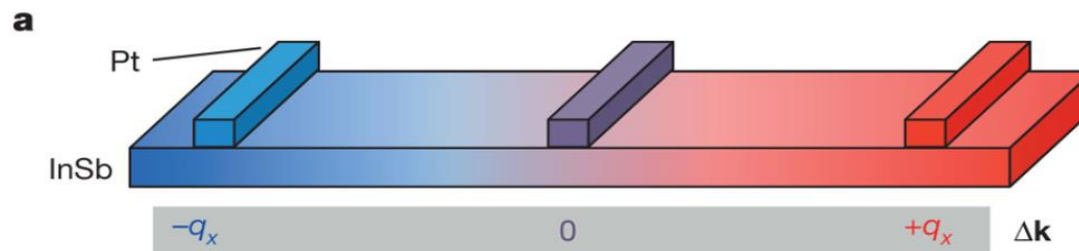
Nature, 455, 2008

Ferromagnetic Semiconductor (2010)



Nature Materials, 9, 2010

Non Magnetic Material (2012)



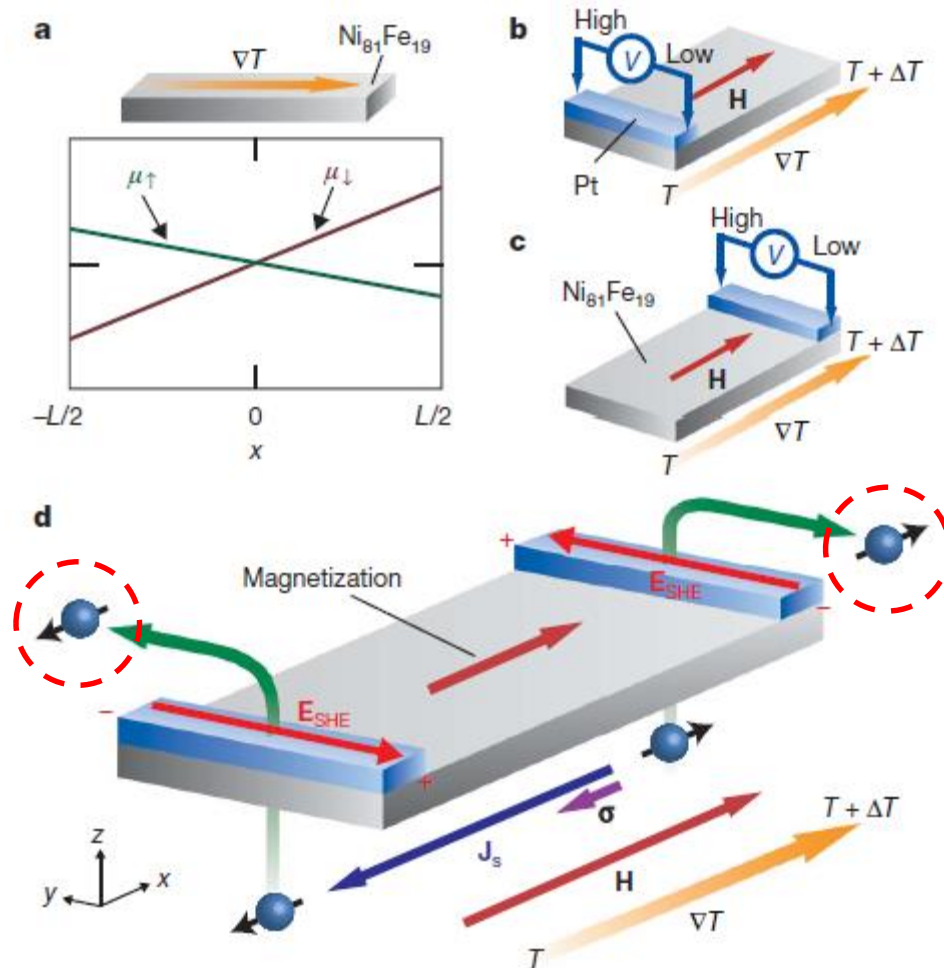
Nature, 487, 2012

2

Mechanism

Principles of Spin Seebeck Effect(SSE)

Structure



Material

- $\text{Ni}_{81}\text{Fe}_{19}$ film: Soft Ferromagnet
- Pt wire: Paramagnet

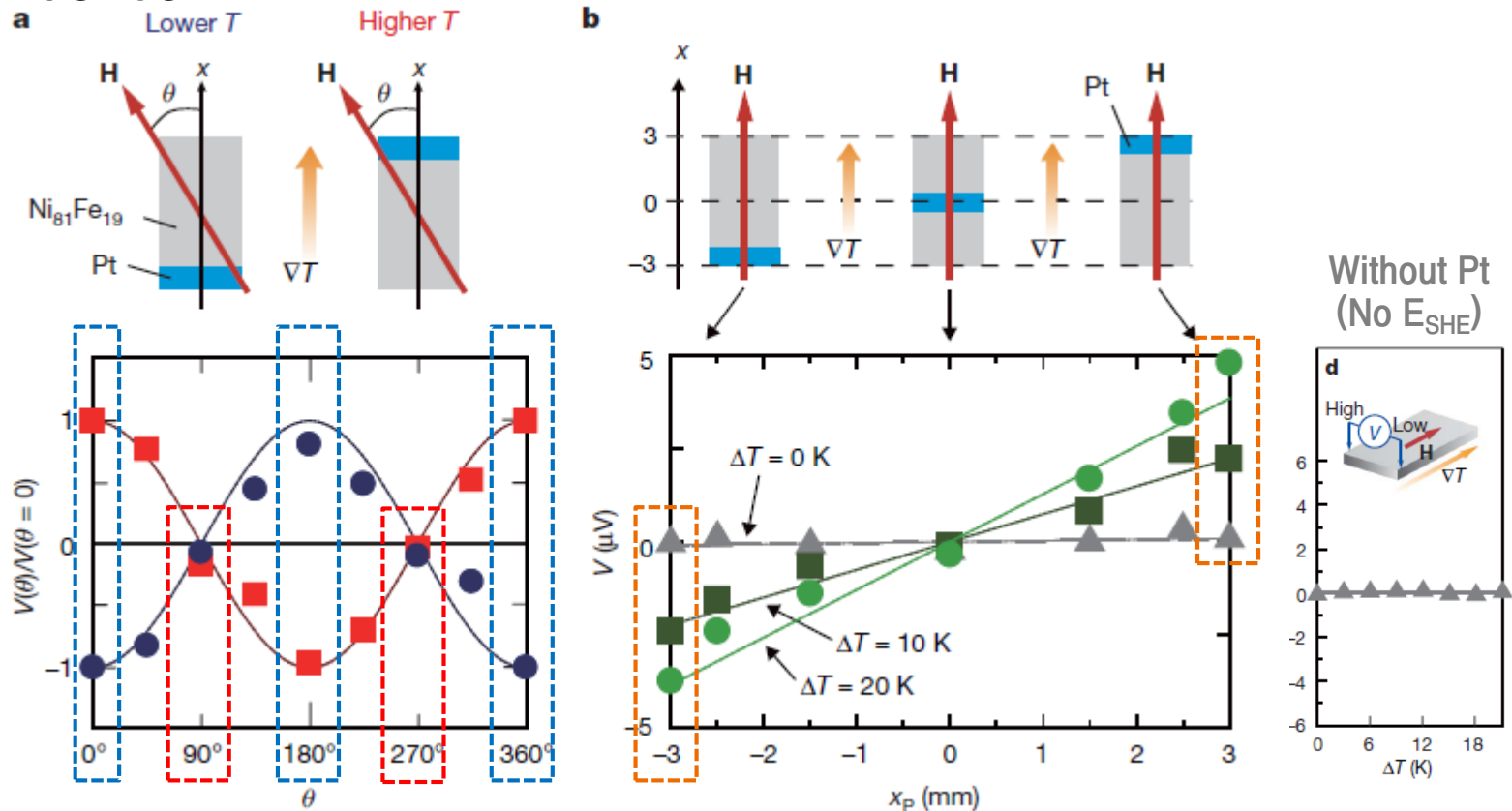
Mechanism

- Film: ΔT ($\text{Ni}_{81}\text{Fe}_{19}$ layer) \rightarrow spin $V \rightarrow$ spin current (Pt layer)
- Wire: Spin current \rightarrow ISHE

Related Principle

- Inverse Spin Hall Effect (ISHE)
: spin current \rightarrow Electromotive force

Dependence



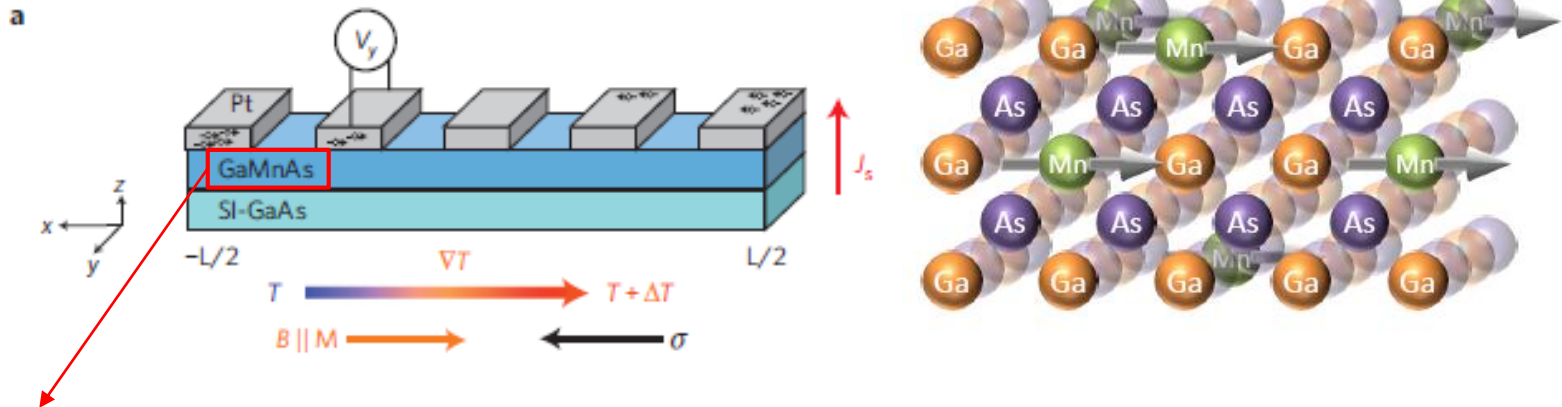
[Angle] : spin V varies with θ

- Consistent with the Prediction of the ISHE

[Position] : spin $V \propto \Delta T, x_P$

- Spins can be extracted from every position of film surface (by attaching a metal contact)

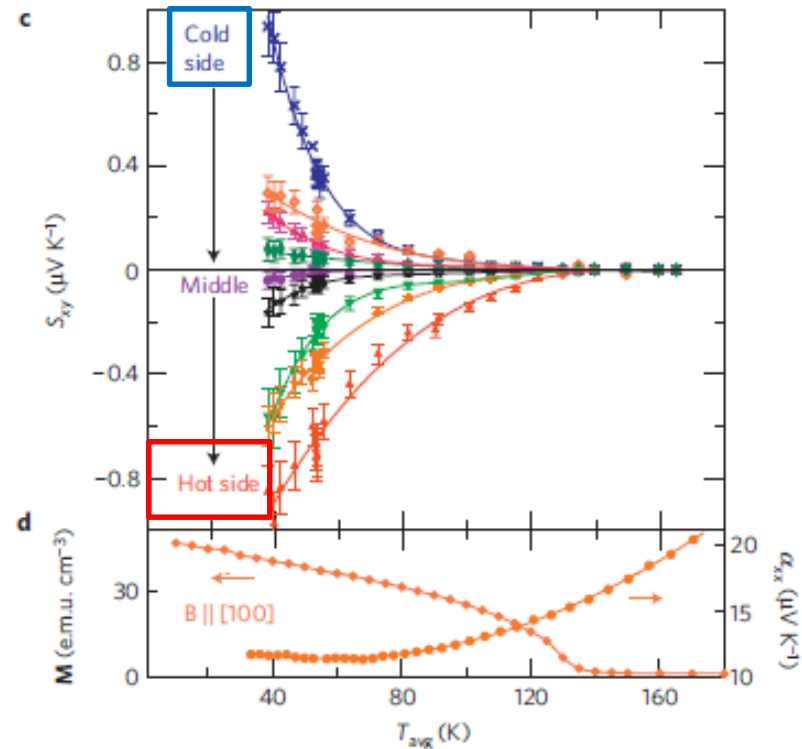
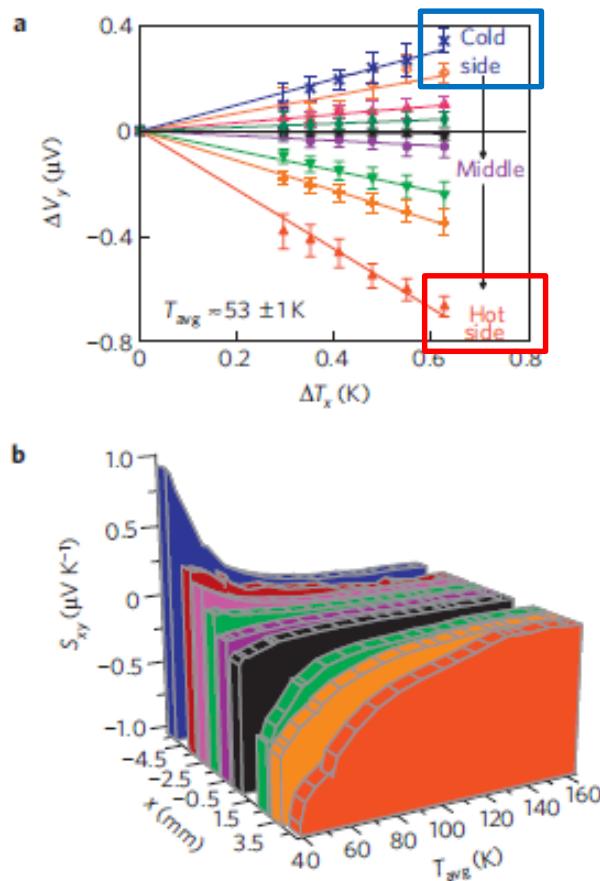
Structure



GaMnAs: Ferromagnetic Semiconductor

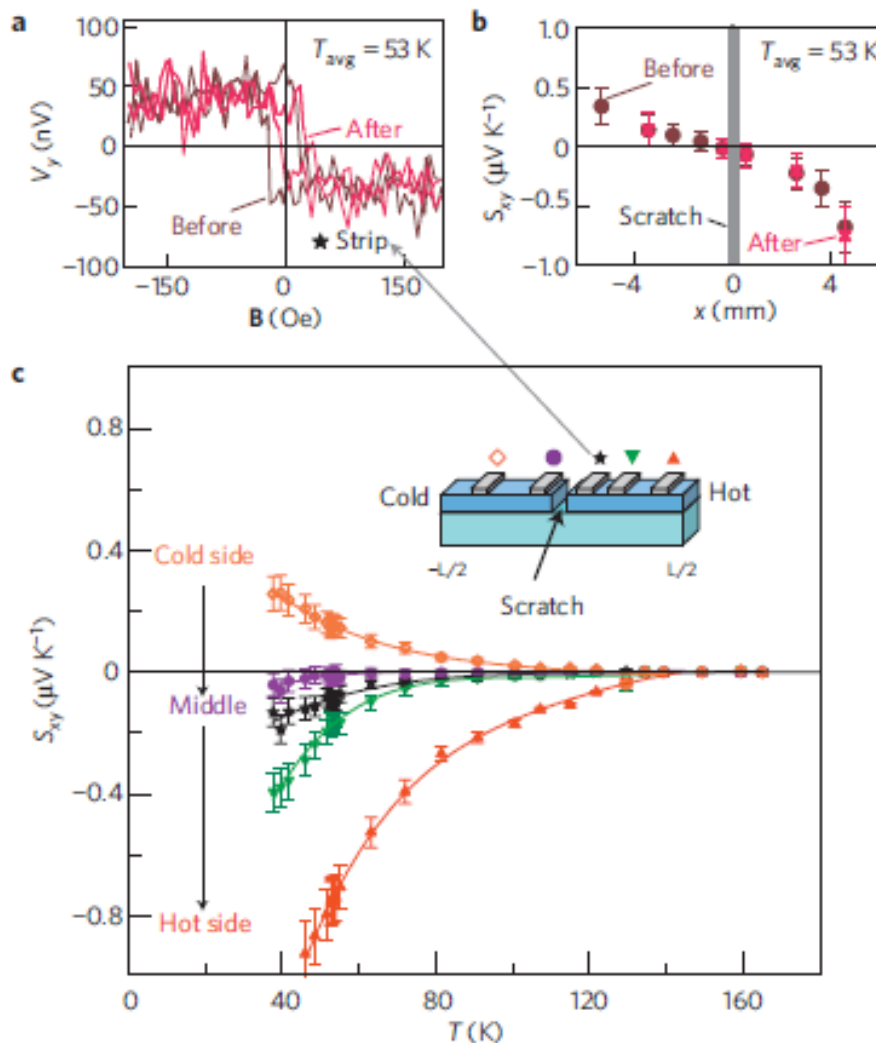
- Much higher fraction of spin-polarized carriers
(GaMnAs $> 85\%$, NiFe $\sim 35\%$)
→ **Larger spin polarization**
- Flexible design of **magnetization direction**

Result 1: Different Seebeck Coefficient



\Rightarrow Two ends have different S

Result 2: Longitudinal Spin Current Test



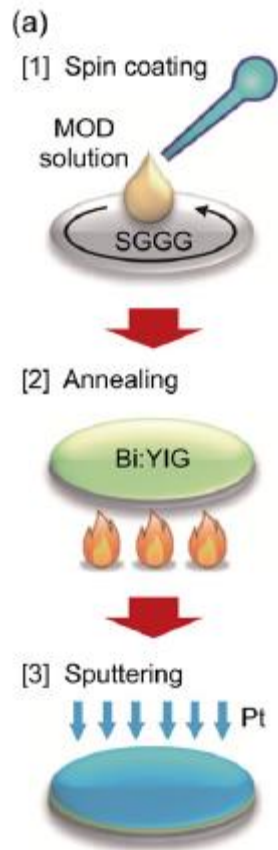
- No qualitative change in signal resulting from the scratch
- Charge/Spin carrier cannot cross
→ SSE is not comes from longitudinal spin current

⇒ Spin Seebeck Effect comes from the ΔT even ferromagnetic -semiconductor

3

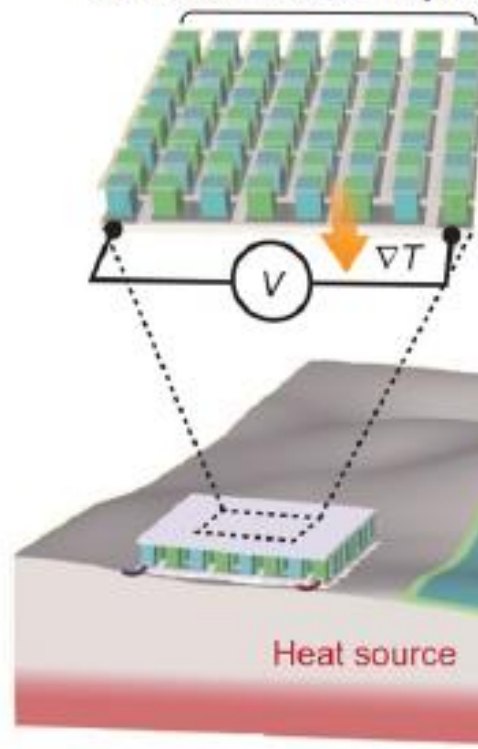
Vista

Future of Spin Seebeck Effect(SSE)

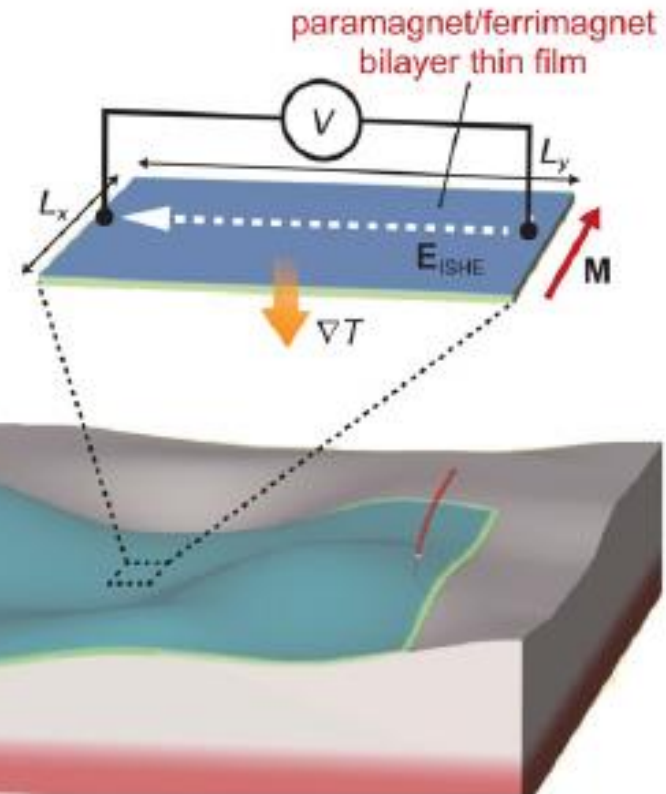


[STE coating]

(a) Seebeck device
series-connected PN junctions



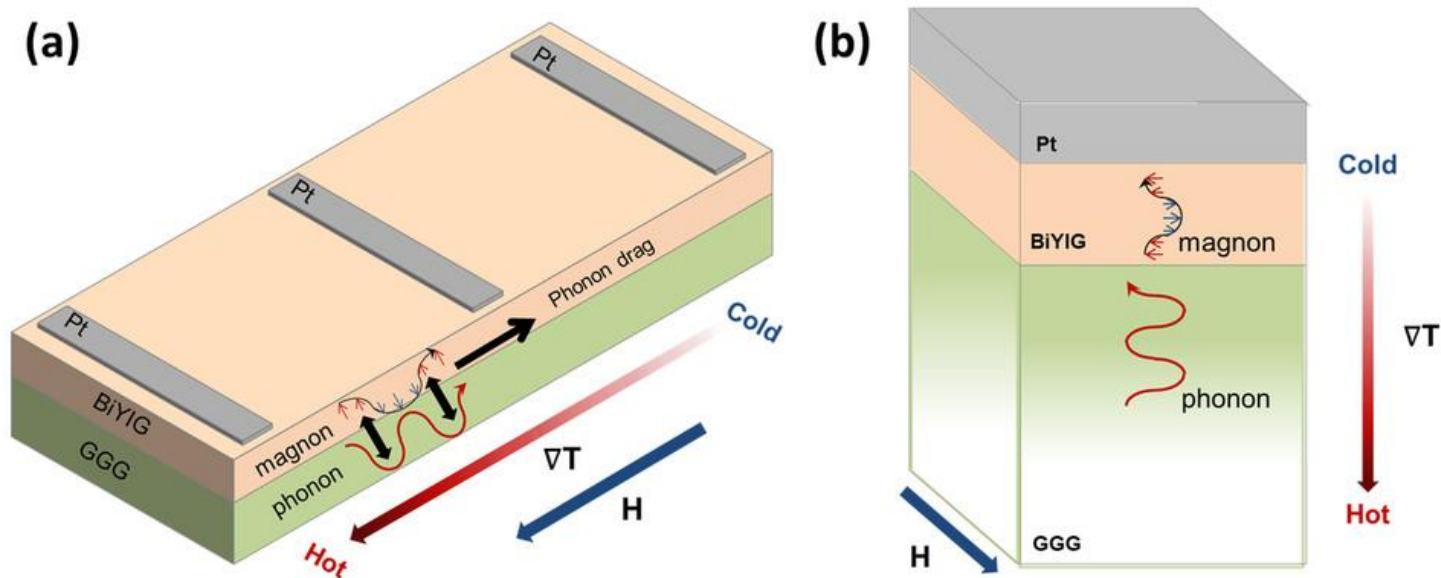
(b) LSSE device (spin thermoelectric coating)



[Seebeck device vs LSSE device]

Simply
process

Able to **coat directly** onto heat sources
with **various shaped surfaces**



- Phonon-drag effect in substrate → **Enhance SSE**
(Only in the transverse geometry)
- Prepared by PLD technique → **Large H_c**

Useful for practical device application

“Minute heat emitted into useful electricity”



Q&A

Thank you for listening

